

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-6 (Canceled)

7. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less in~~ such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;
and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

8. (Previously Presented) A method according to claim 7 wherein said laser beam is an excimer laser beam.

9. (Previously Presented) A method according to claim 7 wherein said semiconductor device is a liquid crystal display device.

10.(Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less~~ and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;
and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

11. (Previously Presented) A method according to claim 10 wherein said laser beam is an excimer laser beam.

12. (Previously Presented) A method according to claim 10 wherein said semiconductor device is a liquid crystal display device.

13. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a lower surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less~~ in such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;

and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

14. (Previously Presented) A method according to claim 13 wherein said laser beam is an excimer laser beam.

15. (Previously Presented) A method according to claim 13 wherein said semiconductor device is a liquid crystal display device.

16. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less~~ and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;

and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

17. (Previously Presented) A method according to claim 16 wherein said laser beam is an excimer laser beam.

18. (Previously Presented) A method according to claim 16 wherein said semiconductor device is a liquid crystal display device.

19. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less~~ in such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;
and

irradiating the crystallized semiconductor film over said substrate provided on said stage with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

20. (Previously Presented) A method according to claim 19 wherein said laser beam is an excimer laser beam.

21. (Previously Presented) A method according to claim 19 wherein said semiconductor device is a liquid crystal display device.

22. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less~~ and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;
and

irradiating the crystallized semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

23. (Previously Presented) A method according to claim 22 wherein said laser beam is an excimer laser beam.

24. (Previously Presented) A method according to claim 22 wherein said semiconductor device is a liquid crystal display device.

25. (Previously Presented) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;

heating said substrate and said semiconductor film, wherein said heating deforms said substrate and said semiconductor film from flat to curved;

flattening said substrate by cooling; and
irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam.

26. (Previously Presented) A method according to claim 25 wherein said laser beam is an excimer laser beam.

27. (Previously Presented) A method according to claim 25 wherein at least a part of the flattened substrate constitutes the liquid crystal display device.

28. (Previously Presented) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;
heating said substrate to crystallize said semiconductor, wherein said heating deforms said substrate and said semiconductor film from flat to curved;
flattening said substrate by cooling; and
irradiating the crystallized semiconductor film with a laser beam.

29. (Previously Presented) A method according to claim 28 wherein said laser beam is an excimer laser beam.

30. (Previously Presented) A method according to claim 28 wherein at least a part of the flattened substrate constitutes the liquid crystal display device.

31-36 (Canceled)

37. (Previously Presented) A method according to claim 7 wherein said substrate is a glass substrate.

38. (Previously Presented) A method according to claim 10 wherein said substrate is a glass substrate.

39. (Previously Presented) A method according to claim 13 wherein said substrate is a glass substrate.

40. (Previously Presented) A method according to claim 16 wherein said substrate is a glass substrate.

41. (Previously Presented) A method according to claim 19 wherein said substrate is a glass substrate.

42. (Previously Presented) A method according to claim 22 wherein said substrate is a glass substrate.

43. (Previously Presented) A method according to claim 25 wherein said substrate is a glass substrate.

44. (Previously Presented) A method according to claim 28 wherein said substrate is a glass substrate.

45. (Previously Presented) A method according to claim 7 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

46. (Previously Presented) A method according to claim 10 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

47. (Previously Presented) A method according to claim 13 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

48. (Previously Presented) A method according to claim 16 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

49. (Previously Presented) A method according to claim 19 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

50. (Previously Presented) A method according to claim 22 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

51. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less in~~
such a manner that a lower surface of said substrate is in contact with said stage;

fixing said substrate by a pusher;

flattening said substrate by vacuum-sucking said lower surface of said substrate;
and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

52. (Previously Presented) A method according to claim 51 wherein said laser beam is an excimer laser beam.

53. (Previously Presented) A method according to claim 51 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

54. (Previously Presented) A method according to claim 51 wherein said substrate is a glass substrate.

55. (Previously Presented) A method according to claim 51 wherein said semiconductor device is a liquid crystal display device.

56. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;
heating said semiconductor film;
setting said substrate onto a stage ~~having a surface roughness of 5 μ m or less in~~
such a manner that a lower surface of said substrate is in contact with said stage;
fixing said substrate by a pusher;
flattening said substrate by vacuum-sucking said lower surface of said substrate;
and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

57. (Previously Presented) A method according to claim 56 wherein said laser beam is an excimer laser beam.

58. (Previously Presented) A method according to claim 56 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

59. (Previously Presented) A method according to claim 56 wherein said substrate is a glass substrate.

60. (Previously Presented) A method according to claim 56 wherein said semiconductor device is a liquid crystal display device.

61. (New) A method according to claim 7 wherein said stage has a surface roughness of 5 μm or less.

62. (New) A method according to claim 10 wherein said stage has a surface roughness of 5 μm or less.

63. (New) A method according to claim 13 wherein said stage has a surface roughness of 5 μm or less.

64. (New) A method according to claim 16 wherein said stage has a surface roughness of 5 μm or less.

65. (New) A method according to claim 19 wherein said stage has a surface roughness of 5 μm or less.

66. (New) A method according to claim 22 wherein said stage has a surface roughness of 5 μm or less.

67. (New) A method according to claim 51 wherein said stage has a surface roughness of 5 μm or less.

68. (New) A method according to claim 56 wherein said stage has a surface roughness of 5 μm or less.